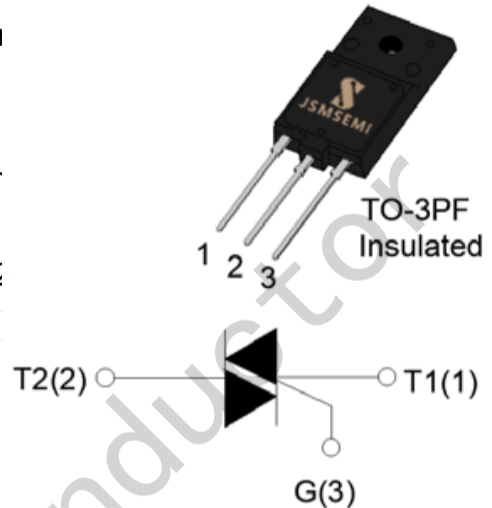


DESCRIPTION:

The JSM41F-800BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JSM41F-800BW snubberless triac is especially recommended for use on inductive loads. By using an external plastic package, JSM41F-800BW provides a rated insulation voltage of 2 VRMS, complying with UL standards (File ref: E252906 Package TO-3PF is RoHS compliant).



Symbol	Value	Unit
$I_{T(RMS)}$	40	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\ I/II/III}$	50/50/50	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	800	V
RMS on-state current ($T_c \leq 66^{\circ}C$)	$I_{T(RMS)}$	40	A
Non repetitive surge peak on-state current (full cycle , $t_p=20ms$, $T_j=25^{\circ}C$)	I_{TSM}	420	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$, $T_j=25^{\circ}C$)		462	
I^2t value for fusing ($t_p=10ms$, $T_j=25^{\circ}C$)	I^2t	1000	A ² s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=125^{\circ}C$)	di/dt	100	A/ μs
Peak gate current ($t_p=20\mu s$, $T_j=125^{\circ}C$)	I_{GM}	8	A

Average gate power dissipation ($T_j=125^{\circ}\text{C}$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	40	W
Peak pulse voltage ($T_j=25^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	1.5	kV

ELECTRICAL CHARACTERISTICS($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX.	50	mA
V_{GT}		I - II -III	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX.	80	mA
		II		200	
I_H	$I_T=500\text{mA}$		MAX.	100	mA
dV/dt	$V_D=540\text{V}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN.	2000	V/ μs
(dI/dt) _c	(dV/dt) _c =20V/ μs $T_j=125^{\circ}\text{C}$		MIN.	25	A/ms
t_{on}	$I_G=80\text{mA } I_A=400\text{mA } I_R=40\text{mA}$ $T_j=25^{\circ}\text{C}$		TYP.	10	μs
t_{off}				70	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=60\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.4	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.73	V
R_D	Dynamic resistance	$T_j=125^{\circ}\text{C}$	10	m Ω
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.13	$^{\circ}\text{C/W}$
$R_{th(j-a)}$	junction to ambient (AC)	50	$^{\circ}\text{C/W}$

FIG.1 Maximum power dissipation versus RMS on-state current

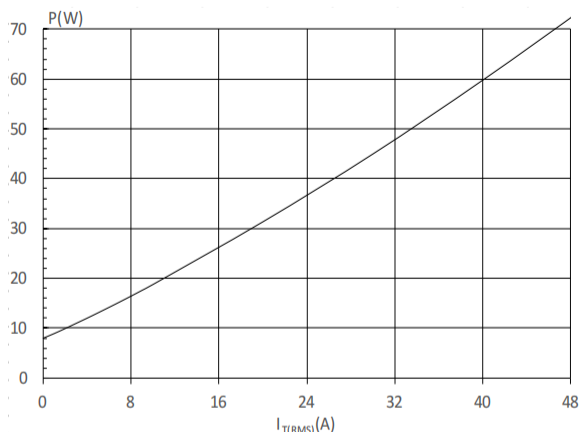


FIG.3: Surge peak on-state current versus number of cycles

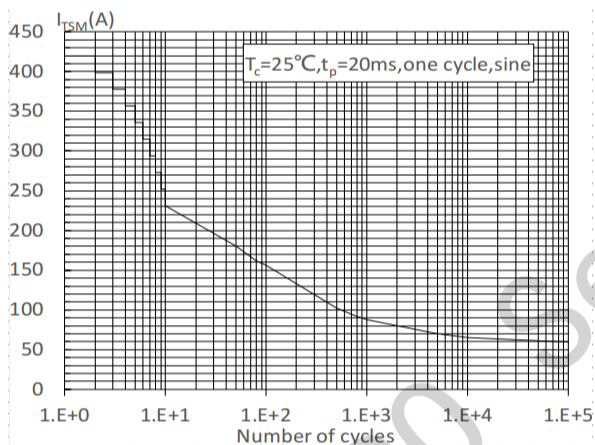


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

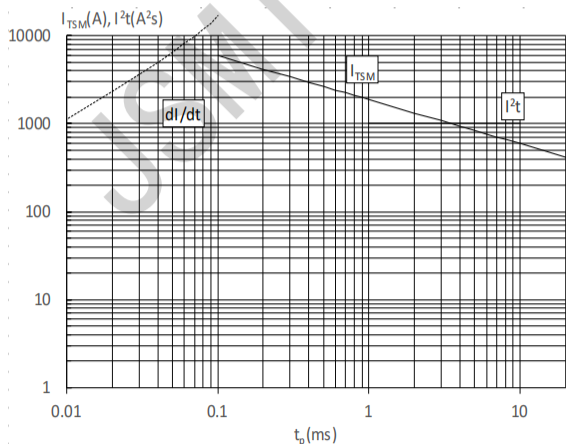


FIG.2: RMS on-state current versus case temperature

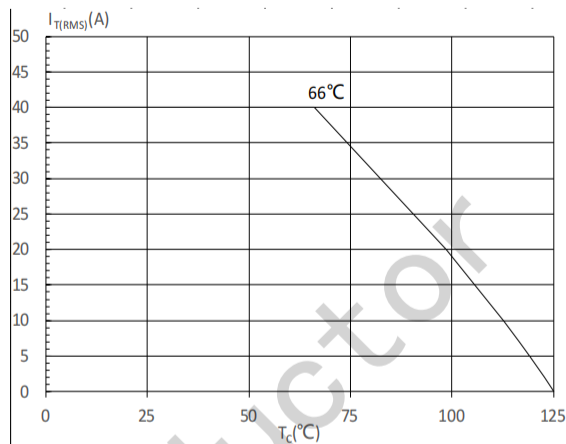


FIG.4: On-state characteristics

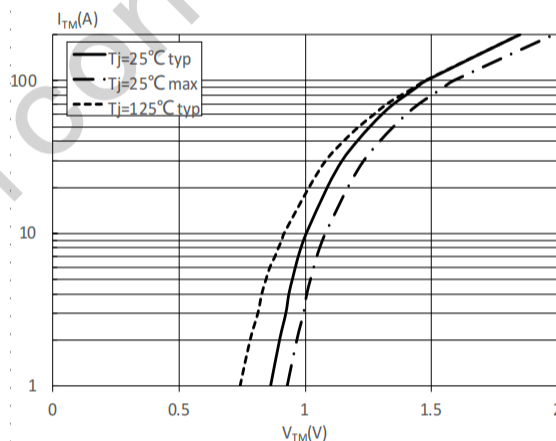


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

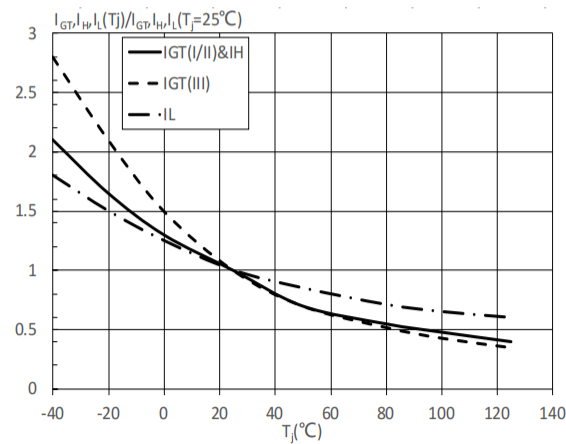
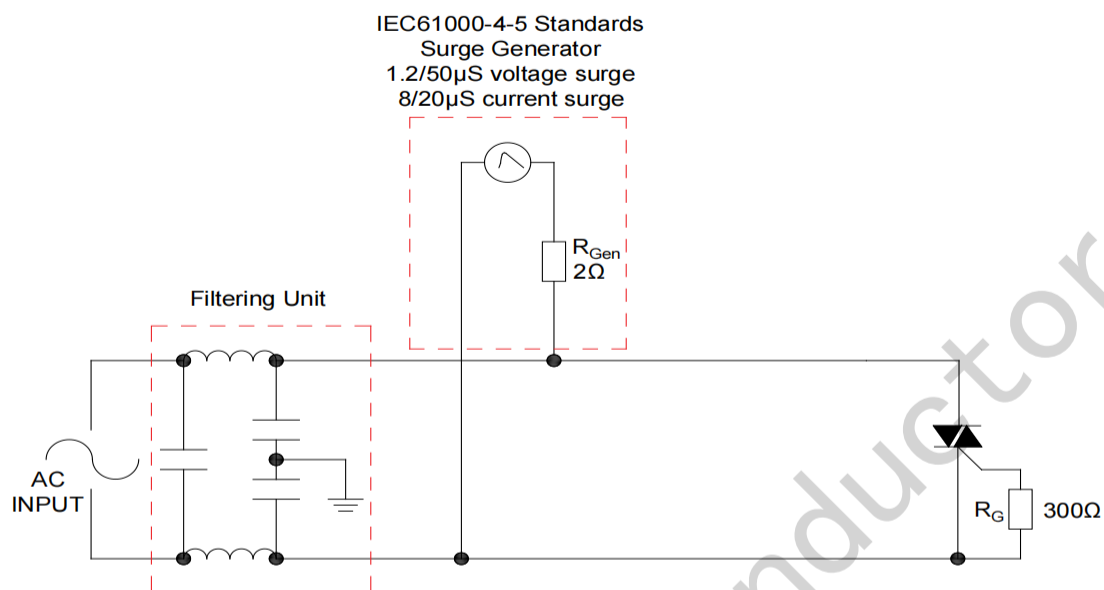


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



PACKAGE MECHANICAL DATA

